Proceedings of
The 18th International Symposium on
Power Semiconductor Devices & ICs

June 4\textsuperscript{th}-8\textsuperscript{th}, 2006

University of Naples Federico II
Naples, ITALY
TECHNICAL SESSIONS

Monday, June 5th 2006

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Claudio Contiero – ST Microelectronics, Italy
M.K. Han Seoul National University, Korea

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Toshiba Corporation, Corporate R & D Center, JAPAN

P-2 Power Drive Circuits for Diagnostic Medical Ultrasound
BRUNO HAIDER
General Electric, Niskayuna, USA

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Robert Bosch GmbH, GERMANY

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*TOYOTA CENTRAL R&D LABS. INC. Nagakute, Aichi, JAPAN
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*University of Bremen, Bremen, Germany
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Fuji Electric Advanced Technology, Co. Ltd., Nagano, Japan

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University of Naples “Federico II”, Naples, Italy

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** University of Naples “Federico II”, Naples, Italy.
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Chair: Jose Millan - CNM, Spain
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*Natl. Inst. of Standards and Tech., USA

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Cree, Inc., 4600 Silicon Drive, USA
* Rensselaer Polytechnic Institute, USA
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* Infineon Asia Pacific Pte. Ltd., Singapore
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